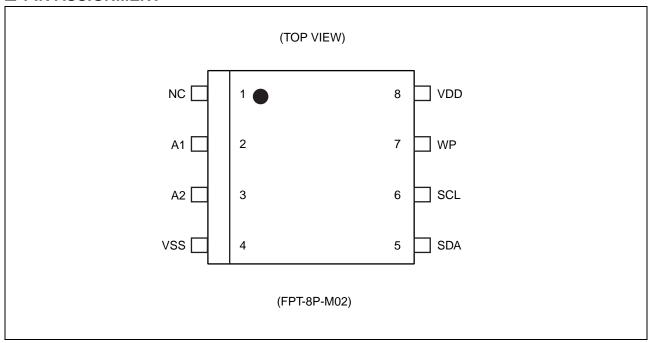
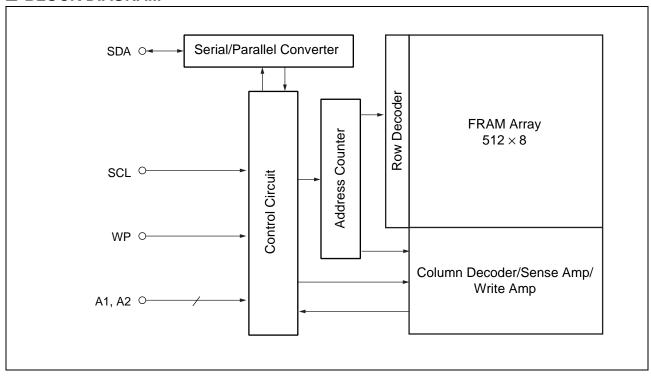
■ PIN ASSIGNMENT



■ PIN FUNCTIONAL DESCRIPTIONS

Pin Number	Pin Name	Functional Description
1	NC	No Connect pin Leave this pin open, or connect to VDD or VSS.
2, 3	A1, A2	Device Address pins The MB85RC04V can be connected to the same data bus up to 4 devices. Device addresses are used in order to identify each of these devices. Connect these pins to VDD pin or VSS pin externally. Only if the combination of VDD and VSS pins matches Device Address Code inputted from the SDA pin, the device operates. In the open pin state, A1 and A2 pins are internally pulled-down and recognized as the "L" level.
4	VSS	Ground pin
5	SDA	Serial Data I/O pin This is an I/O pin which performs bidirectional communication for both memory address and writing/reading data. It is possible to connect multiple devices. It is an open drain output, so a pull-up resistor is required to be connected to the ex- ternal circuit.
6	SCL	Serial Clock pin This is a clock input pin for input/output timing serial data. Data is sampled on the rising edge of the clock and output on the falling edge.
7	WP	Write Protect pin When the Write Protect pin is the "H" level, the writing operation is disabled. When the Write Protect pin is the "L" level, the entire memory region can be overwritten. The reading operation is always enabled regardless of the Write Protect pin input level. The write protect pin is internally pulled down to VSS pin, and that is recognized as the "L" level (write enabled) when the pin is the open state.
8	VDD	Supply Voltage pin

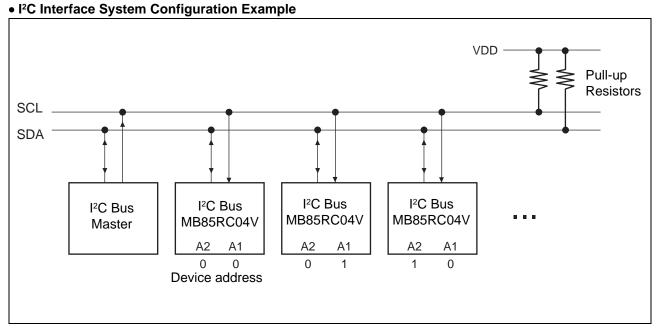
■ BLOCK DIAGRAM



■ I²C (Inter-Integrated Circuit)

The MB85RC04V has the two-wire serial interface; the I²C bus, and operates as a slave device. The I²C bus defines communication roles of "master" and "slave" devices, with the master side holding the authority to initiate control. Furthermore, the I²C bus connection is possible where a single master device is connected to multiple slave devices in a party-line configuration. In this case, it is necessary to assign a unique device address to the slave device, the master side starts communication after specifying the slave

to communicate by addresses.



■ I²C COMMUNICATION PROTOCOL

The I²C bus is a two wire serial interface that uses a bidirectional data bus (SDA) and serial clock (SCL). A data transfer can only be initiated by the master, which will also provide the serial clock for synchronization. The SDA signal should change while SCL is the "L" level. However, as an exception, when starting and stopping communication sequence, SDA is allowed to change while SCL is the "H" level.

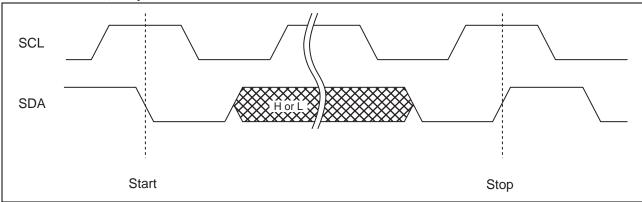
Start Condition

To start read or write operations by the I²C bus, change the SDA input from the "H" level to the "L" level while the SCL input is in the "H" level.

Stop Condition

To stop the I^2C bus communication, change the SDA input from the "L" level to the "H" level while the SCL input is in the "H" level. In the reading operation, inputting the stop condition finishes reading and enters the standby state. In the writing operation, inputting the stop condition finishes inputting the rewrite data and enters the standby state.

• Start Condition, Stop Condition



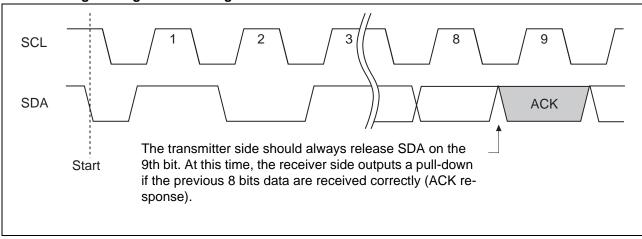
Note: At the write operation, the FRAM device does not need the programming wait time (twc) after issuing the Stop Condition.

■ ACKNOWLEDGE (ACK)

In the I²C bus, serial data including address or memory information is sent in units of 8 bits. The acknowledge signal indicates that every 8 bits of the data is successfully sent and received. The receiver side usually outputs the "L" level every time on the 9th SCL clock after each 8 bits are successfully transmitted and received. On the transmitter side, the bus is temporarily released to Hi-Z every time on this 9th clock to allow the acknowledge signal to be received and checked. During this Hi-Z released period, the receiver side pulls the SDA line down to indicate the "L" level that the previous 8 bits communication is successfully received.

In case the slave side receives Stop condition before sending or receiving the ACK "L" level, the slave side stops the operation and enters to the standby state. On the other hand, the slave side releases the bus state after sending or receiving the NACK "H" level. The master side generates Stop condition or Start condition in this released bus state.





■ MEMORY ADDRESS STRUCTURE

The MB85RC04V has the memory address buffer to store the 9-bit information for the memory address.

As for byte write, page write and random read commands, the complete 9-bit memory address is configured by inputting the memory upper address (1 bit) and the memory lower address (8 bits), and saved to the memory address buffer. Then access to the memory is performed.

As for a current address read command, the complete 9-bit memory address is configured and saved to the memory address buffer, by inputting the memory upper address (1 bit) and the memory lower address (8 bits) which has saved in the memory address buffer. Then access to the memory is performed.

■ DEVICE ADDRESS WORD

Following the start condition, the 8 bit device address word is input. Inputting the device address word decides whether writing or reading operation. However, the clock is always driven by the master. The device address word (8 bits) consists of a device Type code (4 bits), device address code (2 bits), memory upper address code (1 bit), and a Read/Write code (1 bit).

• Device Type Code (4 bits)

The upper 4 bits of the device address word are a device type code that identifies the device type, and are fixed at "1010" for the MB85RC04V.

Device Address Code (2 bits): A1, A2

Following the device type code, the 2 bits of the device address code are input in order of A2 and A1.

The device address code identifies one device from up to 4 devices connected to the bus.

Each MB85RC04V is given a unique 2 bits code on the device address pin (external hardware pin A2 and A1). The slave only responds if the received device address code is equal to this unique 2 bits code.

• Memory Upper Address Code (1 bit): A8

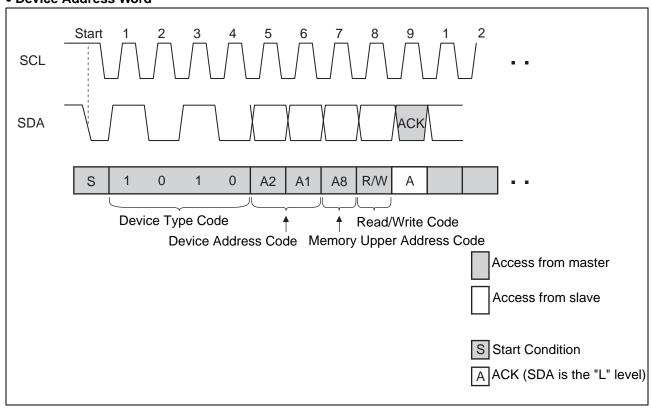
Following the device address code, the 1-bit memory upper address code are input.

This bit is not the setting bit for the slave address, but the upper 1-bit setting bit for the memory address.

Read/Write Code (1 bit)

The 8th bit of the device address word is the R/W (Read/Write) code. When the R/W code is "0" input, a write operation is enabled, and the R/W code is "1" input, a read operation is enabled for the MB85RC04V. If the device type code is not "1010" or the device address code is not equal to the setting of the external device address pins, the Read/Write operation is not performed and the standby state is chosen.

• Device Address Word



■ DATA STRUCTURE

The master inputs the device address word (8 bits) following the start condition, and then the slave outputs the Acknowledge "L" level on the 9th bit. After confirming the Acknowledge response, the sequential 8-bit memory lower address is input, to the byte write, page write and random read commands.

As for the current address read command, inputting the memory lower address is not performed, and the address buffer lower 8-bit is used as the memory lower address.

When inputting the memory lower address finishes, the slave outputs the Acknowledge "L" level on the 9th bit again.

Afterwards, the input and the output data continue in 8-bit units, and then the Acknowledge "L" level is output for every 8-bit data.

■ FRAM ACKNOWLEDGE -- POLLING NOT REQUIRED

The MB85RC04V performs the high speed write operations, so any waiting time for an ACK* by the acknowledge polling does not occur.

*: In E²PROM, the Acknowledge Polling is performed as a progress check whether rewriting is executed or not. It is normal to judge by the 9th bit of Acknowledge whether rewriting is performed or not after inputting the start condition and then the device address word (8 bits) during rewriting.

■ WRITE PROTECT (WP)

The entire memory array can be write protected by setting the WP pin to the "H" level. When the WP pin is set to the "L" level, the entire memory array will be rewritten. Reading is allowed regardless of the WP pin's "H" level or "L" level.

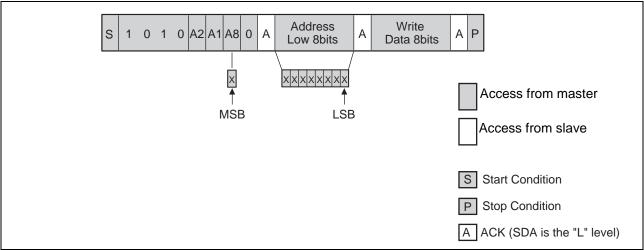
Do not change the WP signal level during the communication period from the start condition to the stop condition.

Note: The WP pin is pulled down internally to the VSS pin, therefore if the WP pin is open, the pin status is recognized as the "L" level (write enabled).

■ COMMAND

• Byte Write

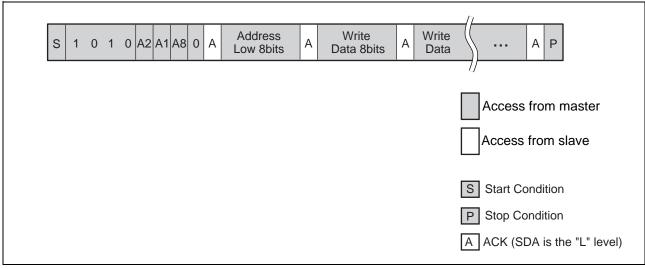
If the device address word (R/W "0" input) is sent after the start condition, the slave responds with an ACK. After this ACK, write memory addresses and write data are sent in the same way, and the write ends by generating a stop condition at the end.



• Page Write

If additional 8 bits are continuously sent after the same command (except stop condition) as Byte Write, a page write is performed. The memory address rolls over to first memory address (000H) at the end of the address. Therefore, if more than 512bytes are sent, the data is overwritten in order starting from the start of the memory address that was written first.

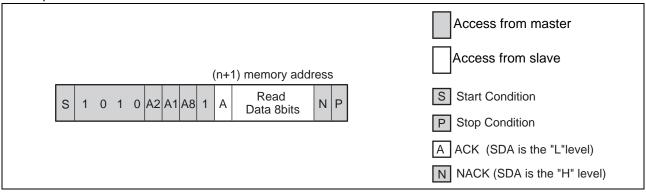
As the FRAM performs the high-speed write operations, the data will be written to FRAM right after the ACK response finished.



· Current Address Read

If the last write or read operation finishes successfully up to the end of stop condition, the memory address that was accessed last remains in the memory address buffer (the length is 9 bits).

When sending this command without turning the power off, it is possible to read from the memory address n+1 which adds 1 to the total 9-bit memory address n, which consists of the 1-bit memory upper address from the device address word input and the lower 8-bit of the memory address buffer. If the memory address n is the last address, it is possible to read with rolling over to the head of the memory address (000H). The current address (address that the memory address buffer indicates) is undefined immediately after turning the power on.

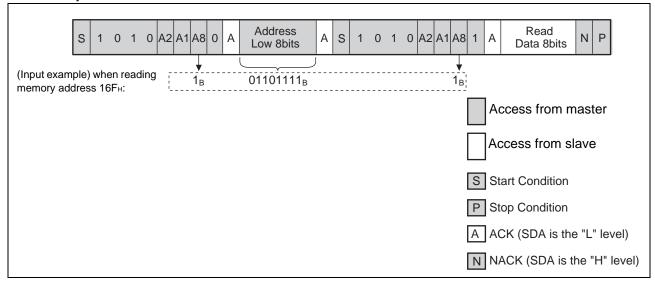


Random Read

The one byte of data from the memory address saved in the memory address buffer can be read out synchronously to SCL by specifying the address in the same way as for a write, and then issuing another start condition and sending the Device Address Word (R/W "1" input).

Setting values for the first and the second memory upper address codes should be the same (an example is shown in below).

The final NACK (SDA is the "H" level) is issued by the receiver that receives the data. In this case, this bit is issued by the master side.



Sequential Read

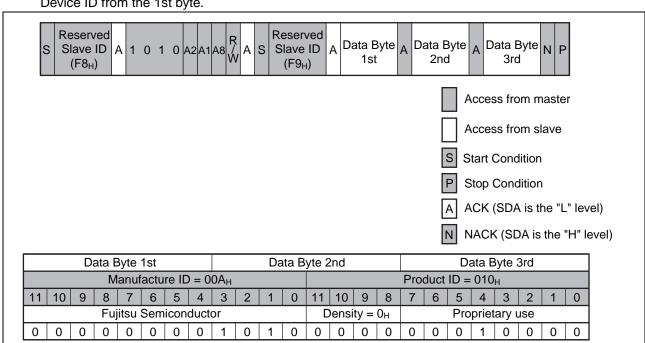
Data can be received continuously following the Device address word (R/W "1" input) after specifying the address in the same way as for Random Read. If the read reaches the end of address, the read address automatically rolls over to the first memory address (000_H) and keeps reading.

				/1			
 А	Read Data 8bits	А	Read Data		 А	Read Data 8bits	N P
				7/			
							Access from master
							Access from slave
						P	Stop Condition
						A	ACK (SDA is the "L" level)
						· 	NACK (SDA is the "H" level)

• Device ID

The Device ID command reads fixed Device ID. The size of Device ID is 3 bytes and consists of manufacturer ID and product ID. The Device ID is read-only and can be read out by following sequences.

- a) The master sends the Reserved Slave ID F8H after the START condition.
- b) The master sends the device address word after the ACK response from the slave. In this device address word, the memory upper address (one bit) and R/W code are "Don't care" value.
- c) The master re-sends the START condition followed by the Reserved Slave ID F9H after the ACK response from the slave.
- d) The master read out the Device ID succeedingly in order of Data Byte 1st / 2nd / 3rd after the ACK response from the slave.
- e) The master responds the NACK (SDA is the "H" level) after reading 3 bytes of the Device ID. In case the master respond the ACK after reading 3 bytes of the Device ID, the master re-reading the Device ID from the 1st byte.

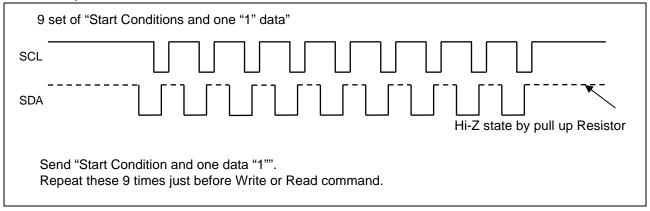


■ SOFTWARE RESET SEQUENCE OR COMMAND RETRY

In case the malfunction has occurred after power on, the master side stopped the I²C communication during processing, or unexpected malfunction has occurred, execute the following (1) software recovery sequence just before each command, or (2) retry command just after failure of each command.

(1) Software Reset Sequence

Since the slave side may be outputting "L" level, do not force to drive "H" level, when the master side drives the SDA port. This is for preventing a bus conflict. The additional hardware is not necessary for this software reset sequence.



(2) Command Retry

Command retry is useful to recover from failure response during I²C communication.

■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Ra	Unit	
Farameter	Зушьог	Min	Max	Oiiit
Power supply voltage*	V _{DD}	- 0.5	+6.0	V
Input voltage*	VIN	- 0.5	$V_{DD} + 0.5 \ (\le 6.0)$	V
Output voltage*	Vouт	- 0.5	$V_{DD} + 0.5 \ (\le 6.0)$	V
Operation ambient temperature	TA	- 40	+ 85	°C
Storage temperature	Tstg	- 55	+ 125	°C

^{*:} These parameters are based on the condition that VSS is 0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Unit			
Farameter	Symbol	Min	Тур	Max		
Power supply voltage*	V _{DD}	3.0	_	5.5	V	
"H" level input voltage*	V _{IH}	$V_{DD} \times 0.8$	_	5.5	V	
"L" level input voltage*	VIL	Vss	_	$V_{DD} \times 0.2$	V	
Operation ambient temperature	TA	- 40	_	+ 85	°C	

^{*:} These parameters are based on the condition that VSS is 0 V.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure. No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

(within recommended operating conditions)

Parameter	Symbol Condition		Value			Unit
Farameter	Syllibol	Condition	Min	Тур	Max	Oilit
Input leakage current*1	lu	$V_{IN} = 0 V to V_{DD}$	_		1	μΑ
Output leakage current*2	ILO	Vout = 0 V to VDD	_	_	1	μΑ
Operating power supply surrent	IDD	SCL = 400 kHz	_	40	80	μΑ
Operating power supply current	IDD	SCL = 1000 kHz	_	90	130	μΑ
Standby current	İsb	SCL, SDA = V_{DD} WP = 0 V or V_{DD} or Open Under Stop Condition $T_A = +25$ °C	_	5	10	μА
"L" level output voltage	Vol	IoL = 3 mA	_	_	0.4	V
Input resistance for	Rın	VIN = VIL (Max)	50	_	_	kΩ
WP, A1, and A2 pins	ININ	VIN = VIH (Min)	1	_	_	МΩ

*1: Applicable pin: SCL,SDA

*2: Applicable pin: SDA

2. AC Characteristics

		Value						
Parameter	Symbol		STANDARD MODE		FAST MODE		MODE US	Unit
		Min	Max	Min	Max	Min	Max	
SCL clock frequency	FSCL	0	100	0	400	0	1000	kHz
Clock high time	Тнідн	4000		600	_	400	_	ns
Clock low time	TLOW	4700		1300	_	600		ns
SCL/SDA rising time	Tr		1000	_	300	_	300	ns
SCL/SDA falling time	Tf		300	_	300	_	100	ns
Start condition hold	THD:STA	4000		600	_	250		ns
Start condition setup	Tsu:sta	4700		600	_	250	_	ns
SDA input hold	T _{HD:DAT}	0		0	_	0	_	ns
SDA input setup	Tsu:dat	250		100	_	100		ns
SDA output hold	T _{DH:DAT}	0		0	_	0		ns
Stop condition setup	Tsu:sto	4000		600	_	250	_	ns
SDA output access after SCL falling	Таа		3000	_	900	_	550	ns
Pre-charge time	T _{BUF}	4700	_	1300	_	500	_	ns
Noise suppression time (SCL and SDA)	Tsp		50	—_	50	—_	50	ns

AC characteristics were measured under the following measurement conditions.

: V_{DD}/2

Power supply voltage : STANDARD MODE and FAST MODE 3.0 V to 5.5 V

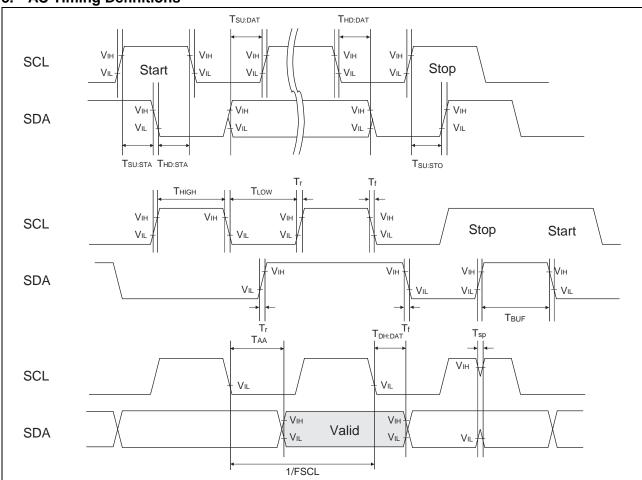
: FAST MODE PLUS 4.5 V to 5.5 V

Operation ambient temperature : -40 °C to +85 °C Input voltage magnitude : $V_{DD} \times 0.2$ to $V_{DD} \times 0.8$

 $\begin{array}{lll} \text{Input rising time} & : 5 \text{ ns} \\ \text{Input falling time} & : 5 \text{ ns} \\ \text{Input judge level} & : V_{\text{DD}}\!/\!2 \end{array}$

Output judge level

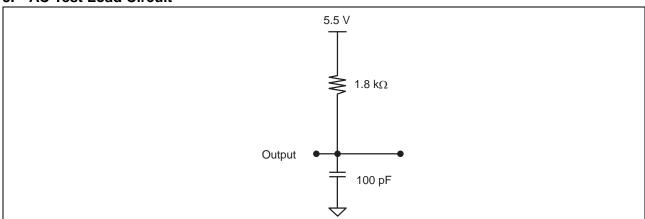
3. AC Timing Definitions



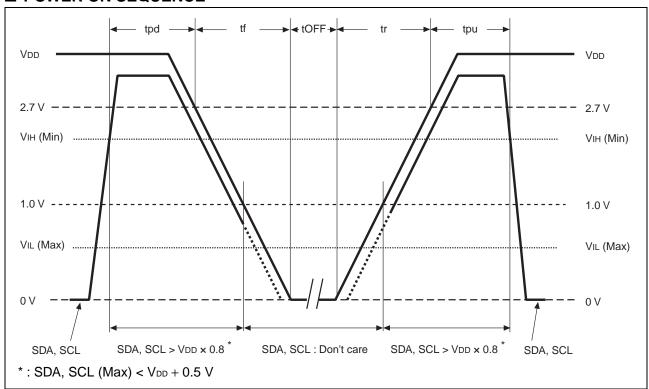
4. Pin Capacitance

Parameter	Symbol	Conditions		Value		Unit
Parameter	Symbol Con	Conditions	Min	Тур	Max	Oilit
I/O capacitance	C _{I/O}	$V_{DD} = V_{IN} = V_{OUT} = 0 V$,	_	_	15	pF
Input capacitance	Cin	f = 1 MHz, T _A = + 25 °C			15	pF

5. AC Test Load Circuit



■ POWER ON SEQUENCE



Parameter	Symbol	Symbol Value		Unit	Condition
raiailletei	Syllibol	Min	Max	Onit	Condition
SDA, SCL level hold time during power down	tpd	85	_	ns	_
SDA, SCL level hold time during	tou	85	_	ns	$V_{DD} = 5.0V \pm 0.5V$ Operation
power up	tpu	0.5	_	ms	$V_{DD} = 3.3V \pm 0.3V$ Operation
Power supply rising time	tr	0.5	50	ms	$V_{DD} = 5.0V \pm 0.5V$ Operation
r ower supply rising time	u	0.005	50	1113	$V_{DD} = 3.3V \pm 0.3V$ Operation
Power supply falling time	tf	0.5	50	ms	_
Power off time	tOFF	50		ms	_

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

■ FRAM CHARACTERISTICS

Item	Min	Max	Unit	Parameter		
Read/Write Endurance*1	1012	_	Times/byte	Operation Ambient Temperature T _A = +85 °C		
	10	_		Operation Ambient Temperature T _A = +85 °C		
Data Retention*2	95	_	Years	Operation Ambient Temperature T _A = +55 °C		
	≥ 200			Operation Ambient Temperature T _A = +35 °C		

^{*1:} Total number of reading and writing defines the minimum value of endurance, as an FRAM memory operates with destructive readout mechanism.

^{*2 :} Minimum values define retention time of the first reading/writing data right after shipment, and these values are calculated by qualification results.

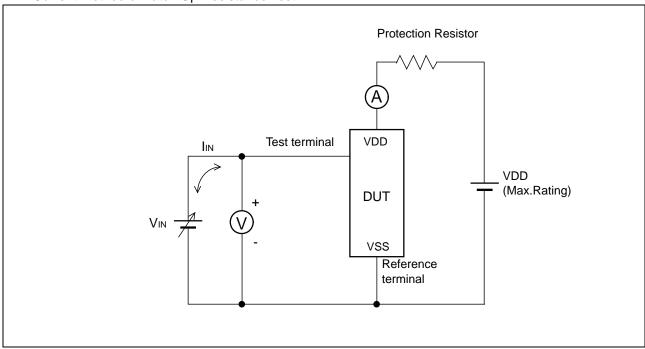
■ NOTE ON USE

- We recommend programming of the device after reflow. Data written before reflow cannot be guaranteed.
- During the access period from the start condition to the stop condition, keep the level of WP, A1, and A2 pins to the "H" level or the "L" level.

■ ESD AND LATCH-UP

Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant		≥ 2000 V
ESD MM (Machine Model) JESD22-A115 compliant		≥ 200 V
ESD CDM (Charged Device Model) JESD22-C101 compliant		_
Latch-Up (I-test) JESD78 compliant	MB85RC04VPNF-G-JNE1	_
Latch-Up (V _{supply} overvoltage test) JESD78 compliant		_
Latch-Up (Current Method) Proprietary method		_
Latch-Up (C-V Method) Proprietary method		≥ 200 V

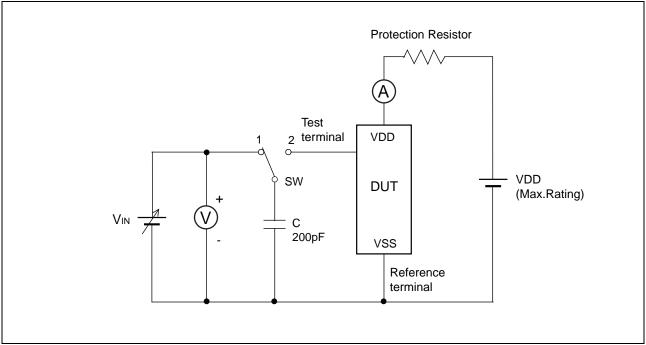
• Current method of Latch-Up Resistance Test



Note: The voltage V_{IN} is increased gradually and the current I_{IN} of 300 mA at maximum shall flow. Confirm the latch up does not occur under $I_{IN} = \pm 300$ mA.

In case the specific requirement is specified for I/O and I_{IN} cannot be 300 mA, the voltage shall be increased to the level that meets the specific requirement.

• C-V method of Latch-Up Resistance Test



Note: Charge voltage alternately switching 1 and 2 approximately 2 sec interval. This switching process is considered as one cycle.

Repeat this process 5 times. However, if the latch-up condition occurs before completing 5times, this test must be stopped immediately.

■ REFLOW CONDITIONS AND FLOOR LIFE

[JEDEC MSL] : Moisture Sensitivity Level 3 (ISP/JEDEC J-STD-020D)

■ CURRENT STATUS ON CONTAINED RESTRICTED SUBSTANCES

This product complies with the regulations of REACH Regulations, EU RoHS Directive and China RoHS. Please refer to the following web site for more details of current status on contained restricted substances in our products.

http://www.fujitsu.com/global/services/microelectronics/environment/products/

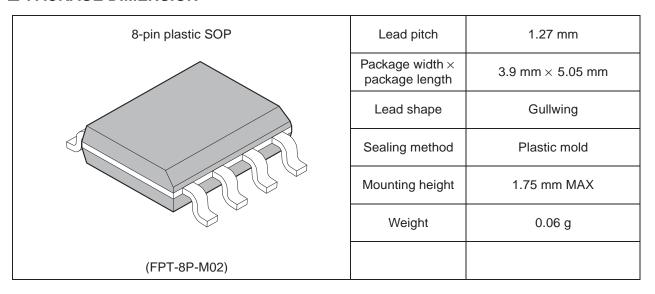
18

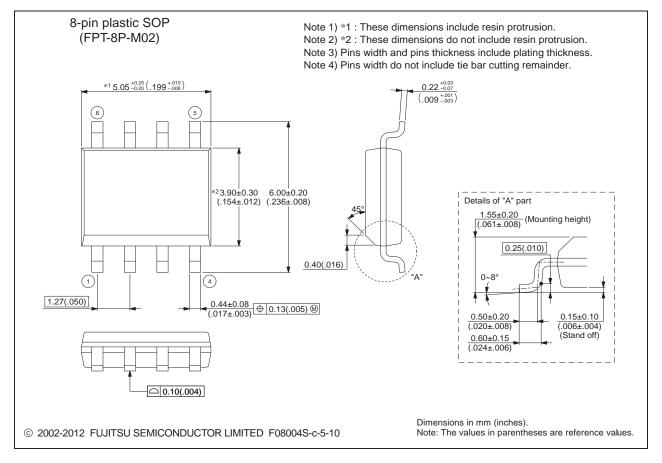
■ ORDERING INFORMATION

Part number	Package	Shipping form	Minimum shipping quantity
MB85RC04VPNF-G-JNE1	8-pin, plastic SOP (FPT-8P-M02)	Tube	*
MB85RC04VPNF-G-JNERE1	8-pin, plastic SOP (FPT-8P-M02)	Embossed Carrier tape	1500

^{*:} Please contact our sales office about minimum shipping quantity.

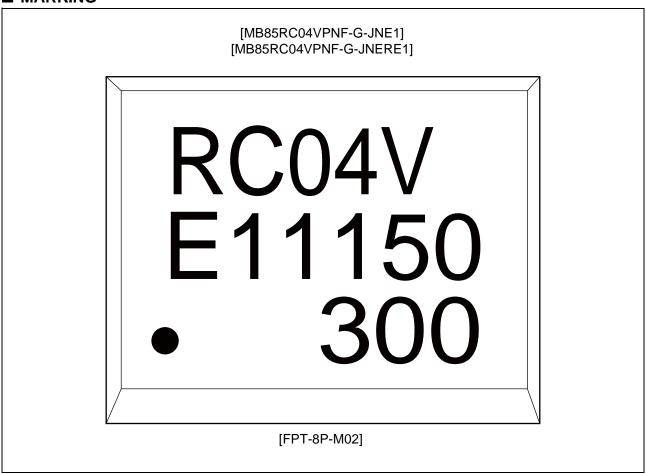
■ PACKAGE DIMENSION





Please check the latest package dimension at the following URL. http://edevice.fujitsu.com/package/en-search/

■ MARKING

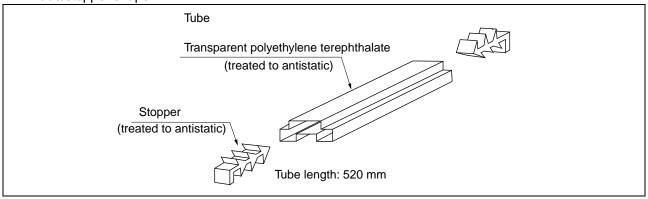


■ PACKING INFORMATION

1. Tube

1.1 Tube Dimensions

• Tube/stopper shape

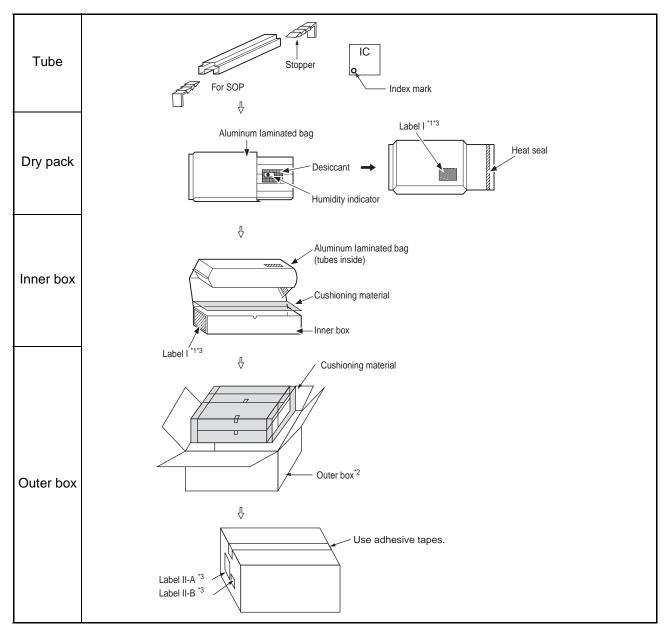


Tube cross-sections and Maximum quantity

		N	laximum qua	antity
Package form	Package code	pcs/ tube	pcs/inner box	pcs/outer box
SOP, 8, plastic (2)	FPT-8P-M02	95	7600	30400
7.4 6.4 				
©2006-2010 FUJITSU SEMICONDUCTOR LIMITED F08008-SET1-PET:FJ99L-0022-E0008-1-K-3				
t = 0.5 Transparent polyethylene terephthalate				

(Dimensions in mm)

1.2 Tube Dry pack packing specifications



^{*1:} For a product of witch part number is suffixed with "E1", a " [G] (N)" marks is display to the moisture barrier bag and the inner boxes.

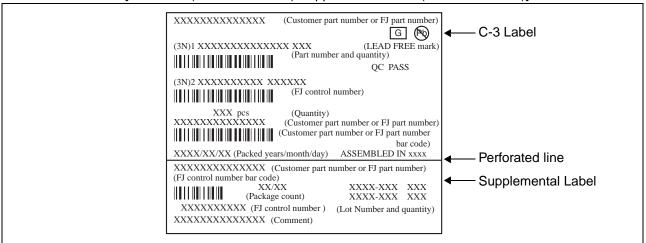
Note: The packing specifications may not be applied when the product is delivered via a distributor.

^{*2:} The space in the outer box will be filled with empty inner boxes, or cushions, etc.

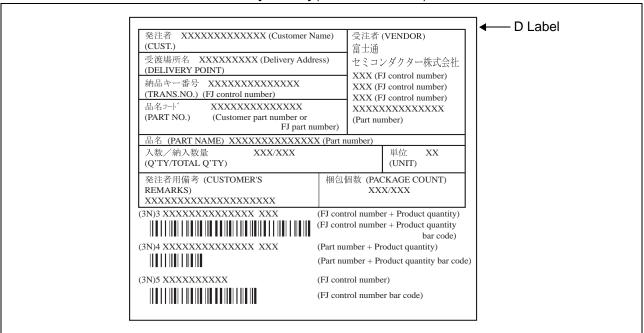
^{*3:} Please refer to an attached sheet about the indication label.

1.3 Product label indicators

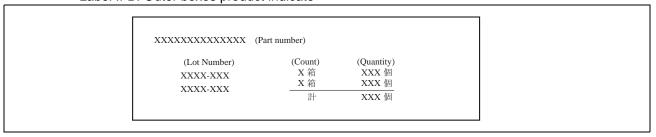
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



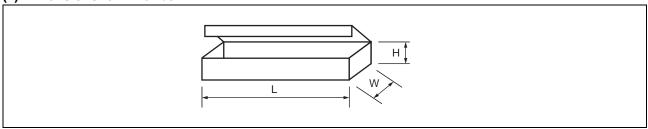
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

1.4 Dimensions for Containers

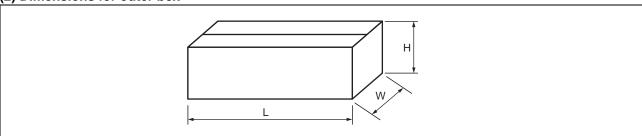
(1) Dimensions for inner box



L	W	Н
540	125	75

(Dimensions in mm)

(2) Dimensions for outer box



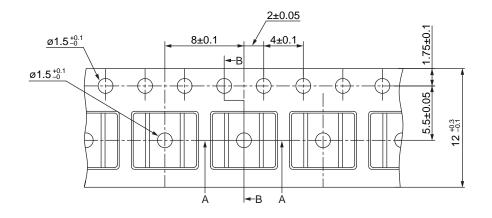
L	W	Н
565	270	180

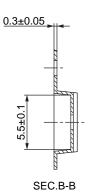
(Dimensions in mm)

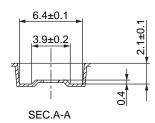
2. Emboss Tape

2.1 Tape Dimensions

PKG code	Reel No	Maximum storage capacity			
1 110 0000	11001110	pcs/reel	pcs/inner box	pcs/outer box	
FPT-8P-M02	3	1500	1500	10500	







© 2012 FUJITSU SEMICONDUCTOR LIMITED SOL8-EMBOSSTAPE9: NFME-EMB-X0084-1-P-1

(Dimensions in mm)

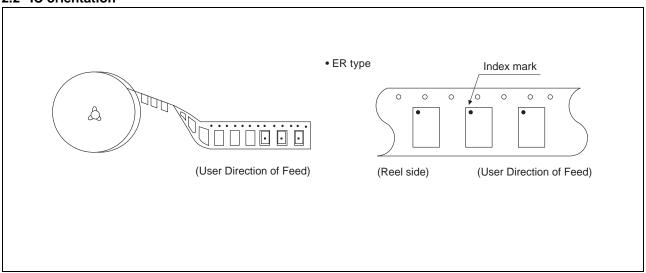
Material: Conductive polystyrene

Heat proof temperature : No heat resistance.

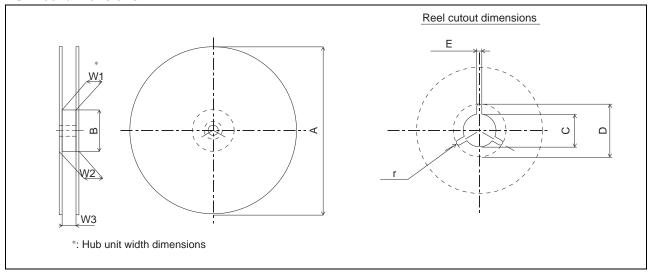
Package should not be baked

by using tape and reel.

2.2 IC orientation



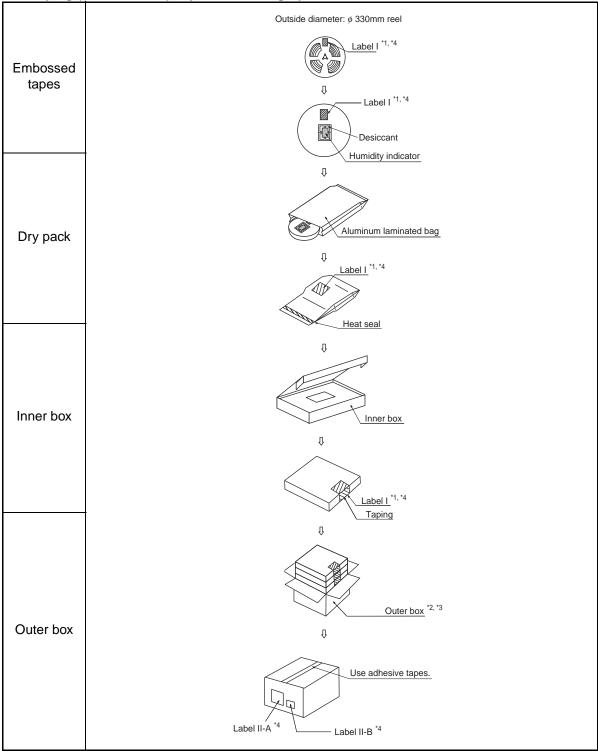
2.3 Reel dimensions



Dimensions in mm

														imensioi	
Reel No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
Tape width Symbol	8	1	2	1	6	2	4	3.	2	4	4	56	12	16	24
Α	254 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2				330) ± 2			
В	100 +2 150							100 -0	100 ± 2						
С		13 ± 0.2 13 ^{+0.5}													
D	21 ± 0.8 20.5 ⁺¹ _{-0.2}														
E	2 ± 0.5														
W1	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$					12.4 +1	16.4 +1	24.4+0.1							
W2	less than 14.4					less than 18.4	less than 22.4	less than 30.4							
W3	7.9 ~ 10.9	11.9 -	~ 15.4	15.9	~ 19.4	23.9 -	~ 27.4	31.9 ~ 35.4		43.9 -	- 47.4	55.9 ~ 59.4	12.4 ~ 14.4	16.4 ~ 18.4	24.4 ~ 26.4
r	1.0														





Note: The packing specifications may not be applied when the product is delivered via a distributor.

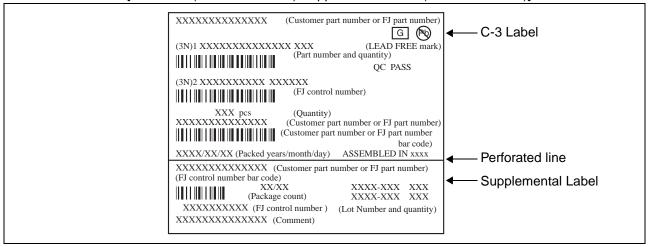
^{*2:} The size of the outer box may be changed depending on the quantity of inner boxes.

^{*3:} The space in the outer box will be filled with empty inner boxes, or cushions, etc.

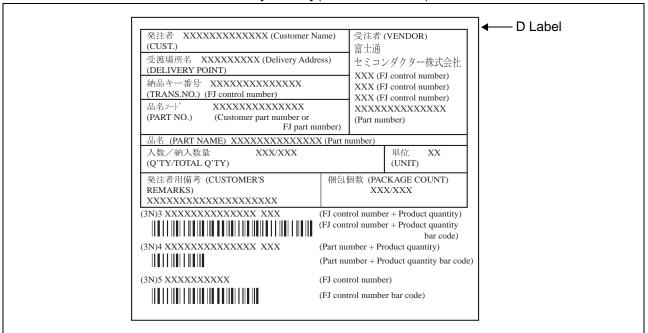
^{*4:} Please refer to an attached sheet about the indication label.

2.5 Product label indicators

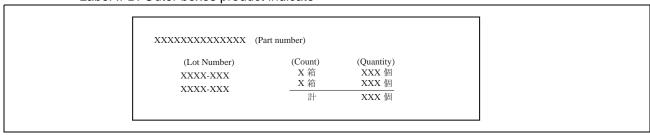
Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



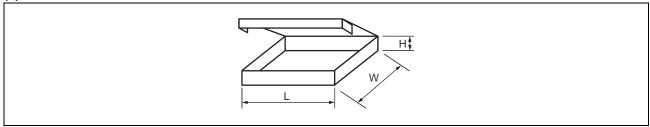
Label II-B: Outer boxes product indicate



Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

2.6 Dimensions for Containers

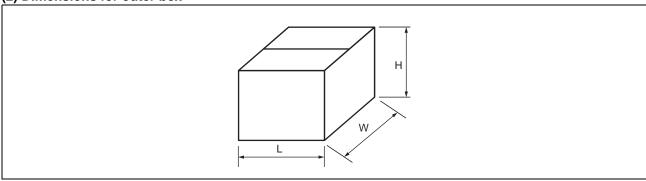
(1) Dimensions for inner box



Tape width	L	W	Н
12, 16	365	345	40
24, 32			50
44		343	65
56			75

(Dimensions in mm)

(2) Dimensions for outer box



L	W	Н
415	400	315

(Dimensions in mm)

■ MAJOR CHANGES IN THIS EDITION

A change on a page is indicated by a vertical line drawn on the left side of that page.

Page	Section	Change Results
16	■ POWER ON/OFF SEQUENCE	Defined values of tpu and tr at operation voltage. Min Max Unit Condition tpu 85 — ns $V_{DD} = 5.0 \text{ V} \pm 0.5 \text{ V}$ Operation 0.5 — ms $V_{DD} = 3.3 \text{ V} \pm 0.3 \text{ V}$ Operation tr 0.5 50 ms $V_{DD} = 5.0 \text{ V} \pm 0.5 \text{ V}$ Operation 0.005 50 ms $V_{DD} = 3.3 \text{ V} \pm 0.3 \text{ V}$ Operation
17	■ NOTE ON USE	Revised the following description: "Data written before performing IR reflow is not guaranteed after IR reflow." — "We recommend programming of the device after reflow. Data written before reflow cannot be guaranteed."
18	■ REFLOW CONDITIONS AND FLOOR LIFE	Revised to following description. [JEDEC MSL] : Moisture Sensitivity Level 3 (ISP/JEDEC J-STD-020D)
	CURRENT STATUS ON CONTAINED RESTRICTED SUBSTANCES	Changed the title and revised the description which refers to a website.
19	■ ORDERING INFORMATION	Changed the Minimum shipping quantity. 1 → —* Added the following note below table. *: Please contact our sales office about minimum shipping quantity.
23	1.2 Tube Dry pack packing specifications	Revised the figure of Dry pack.

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